

Automotive Dual N-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY

V_{DS} (V)	60
$R_{DS(on)}$ (Ω) at $V_{GS} = 10$ V	0.080
I_D (A)	± 3.7
Configuration	Dual

FEATURES

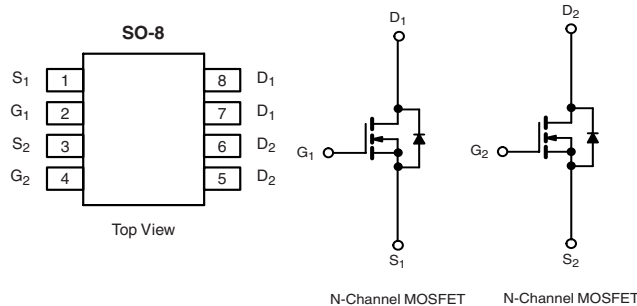
- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance

AEC-Q101 RELIABILITY

- Passed all AEC-Q101 Reliability Testing
- Characterization Ongoing



Available
RoHS*
COMPLIANT



ORDERING INFORMATION

Package	SO-8
Lead (Pb)-free	SQ9945AEY-T1-E3
SnPb	SQ9945AEY-T1

ABSOLUTE MAXIMUM RATINGS $T_C = 25$ °C, unless otherwise noted

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ^a	I_D	$T_C = 25$ °C - 3.7	A
		$T_C = 70$ °C - 3.2	
Continuous Source Current (Diode Conduction) ^a	I_S	2	
Pulsed Drain Current ^b	I_{DM}	25	
Single Pulse Avalanche Energy	E_{AS}	-	mJ
Single Pulse Avalanche Current			
Maximum Power Dissipation ^b	P_D	$T_C = 25$ °C 2.4	W
		$T_A = 70$ °C 1.7	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient	R_{thJA}	-	°C/W
Junction-to-Case (Drain)	R_{thJC}	-	

Notes

- Package limited.
- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %.
- When mounted on 1" square PCB (FR-4 material).

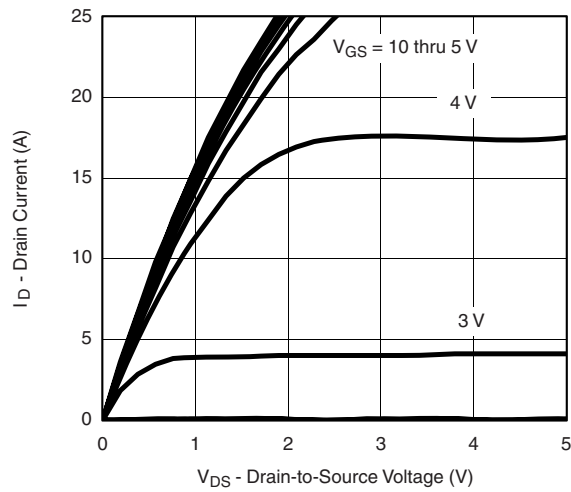
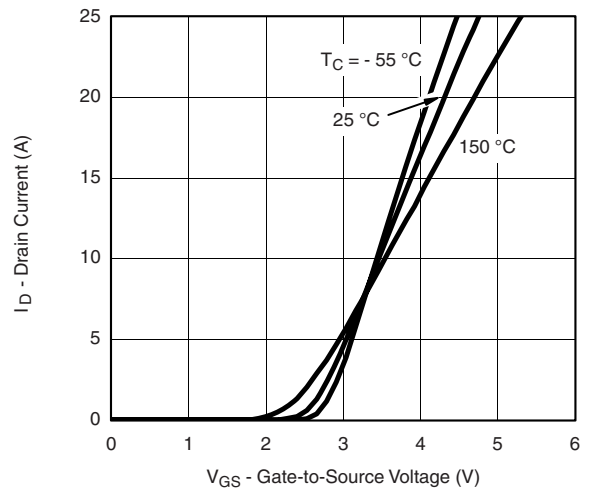
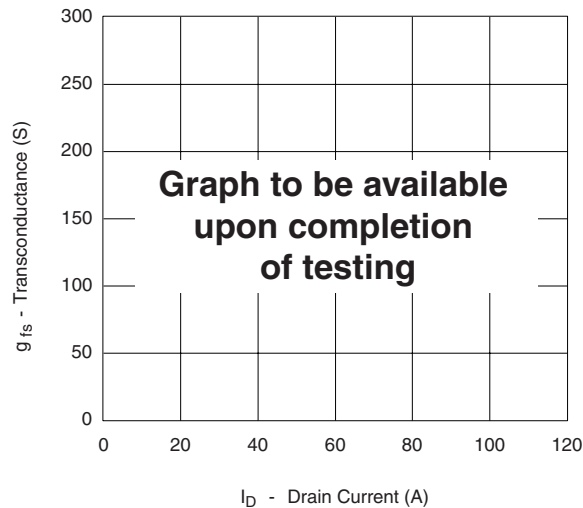
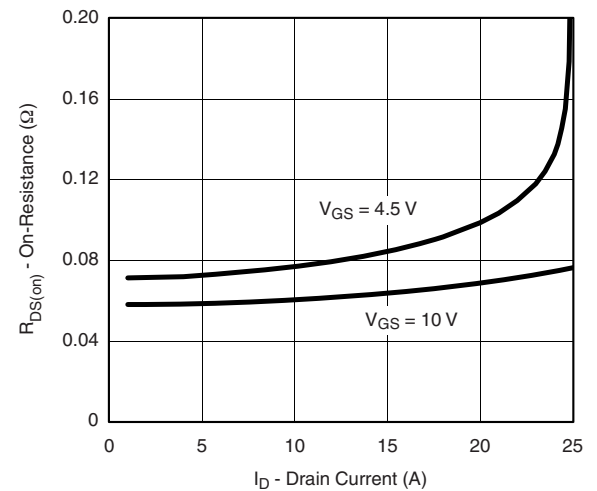
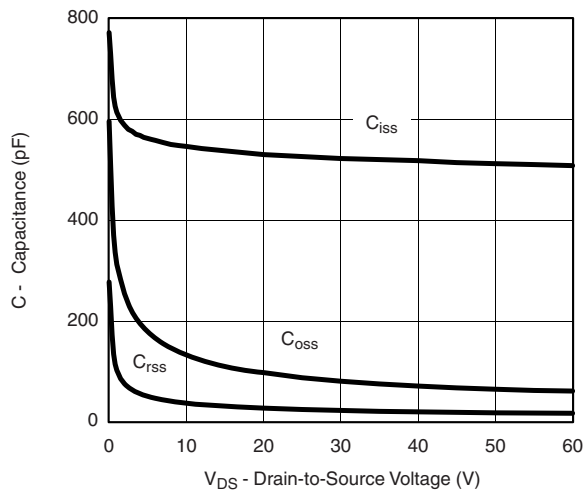
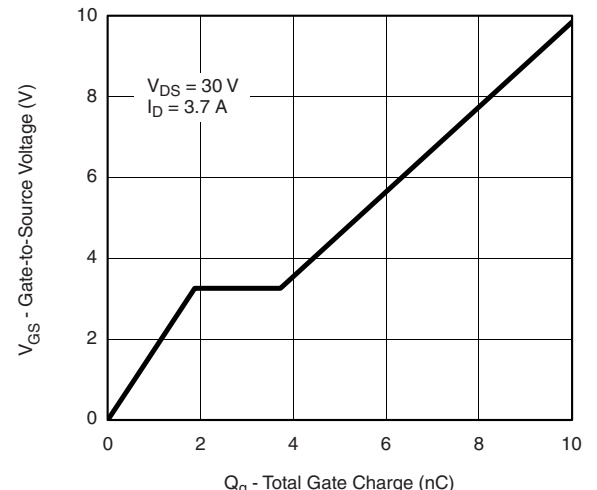
* Pb containing terminations are not RoHS compliant, exemptions may apply

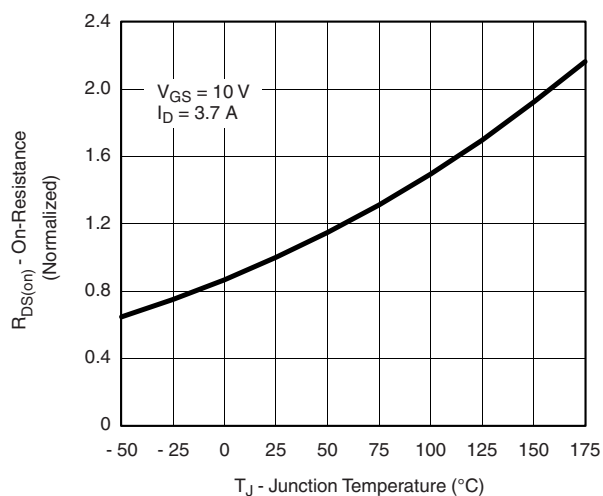
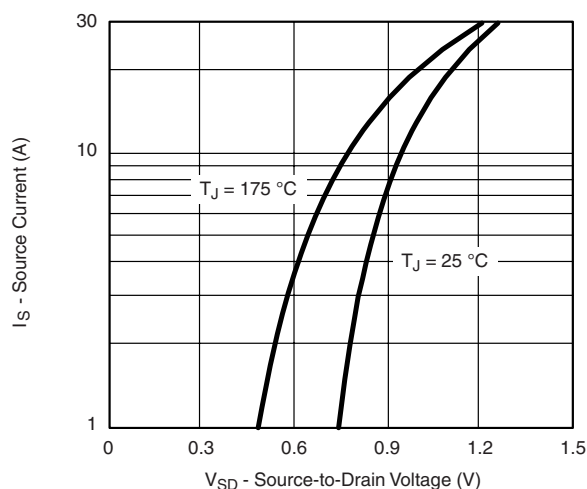
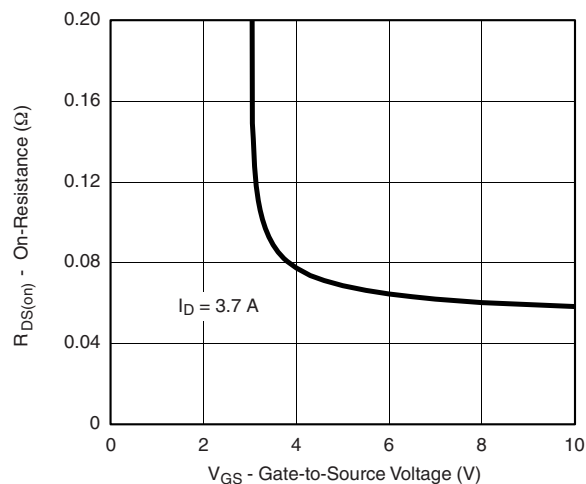
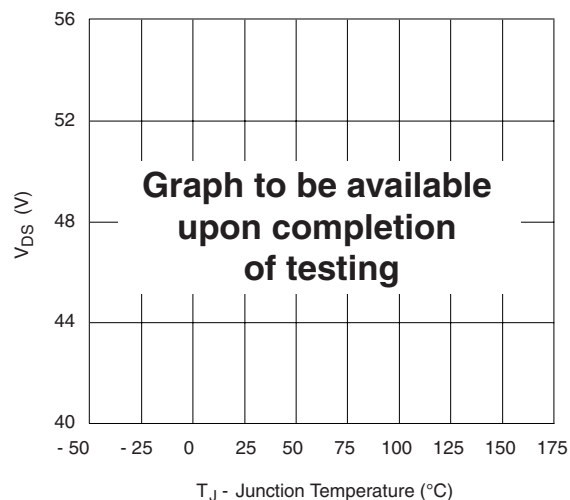
SPECIFICATIONS T _C = 25 °C, unless otherwise noted							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		-	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		1.0	-	3.0	
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 60 V	-	-	1.0	μA
		V _{GS} = 0 V	V _{DS} = 60 V	-	-	10	
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 55 °C	-	-	-	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	V _{DS} ≥ 5 V	20	-	-	A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 3.7 A	-	0.060	0.080	Ω
		V _{GS} = 10 V	I _D = 30 A, T _J = 125 °C	-	-	-	
		V _{GS} = 10 V	I _D = 30 A, T _J = 175 °C	-	-	-	
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 3.7 A		-	-	11	S
Dynamic ^b							
Input Capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	-	-	-	pF
Output Capacitance	C _{oss}			-	-	-	
Reverse Transfer Capacitance	C _{rss}			-	-	-	
Total Gate Charge ^c	Q _g	V _{GS} = 10 V	V _{DS} = 30 V, I _D = 3.7 A	-	11	20	nC
Gate-Source Charge ^c	Q _{gs}			-	2	-	
Gate-Drain Charge ^c	Q _{gd}			-	2	-	
Turn-On Delay Time °	t _{d(on)}	V _{DD} = 30 V, R _L = 30 Ω I _D ≅ 1 A, V _{GEN} = 10 V, R _g = 6 Ω		-	9	20	ns
Rise Time ^c	t _r			-	10	20	
Turn-Off Delay Time ^c	t _{d(off)}			-	21	40	
Fall Time ^c	t _f			-	8	20	
Source-Drain Diode Ratings and Characteristics T _C = 25 °C ^b							
Pulsed Current ^a	I _{SM}			-	-	-	A
Forward Voltage	V _{SD}	I _F = 85 A, V _{GS} = 0 V		-	-	-	V
Reverse Recovery Time	t _{rr}	I _F = 2 A, dI/dt = 100 A/μs		-	45	80	ns
Peak Reverse Recovery Current	I _{RM(REC)}			-	-	-	A
Reverse Recovery Charge	Q _{rr}			-	-	-	μC

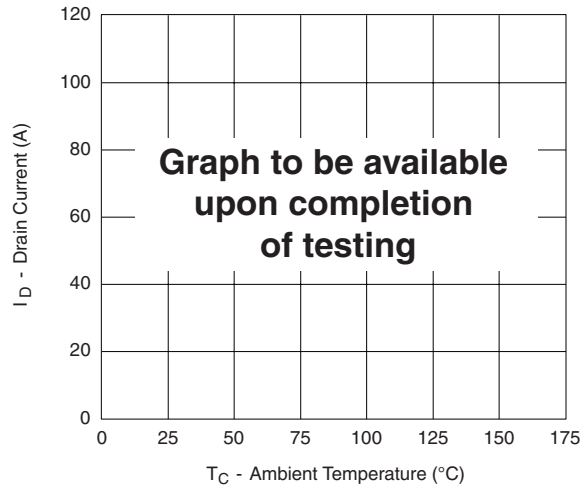
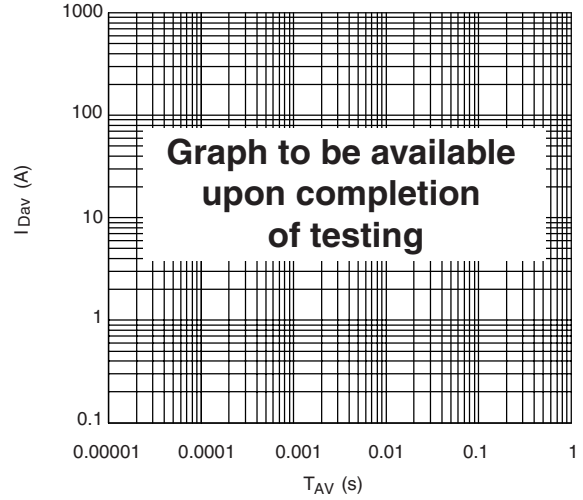
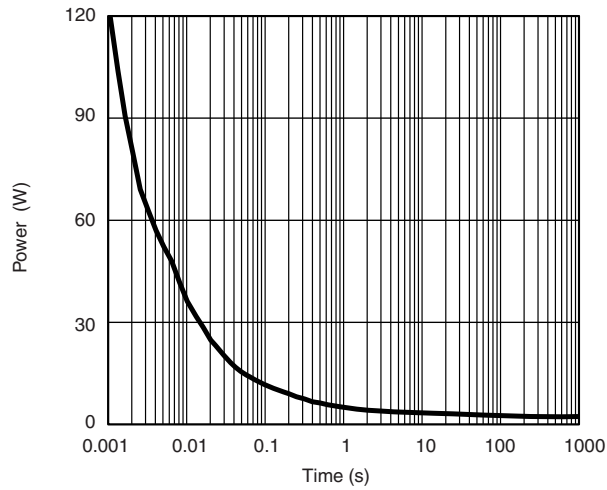
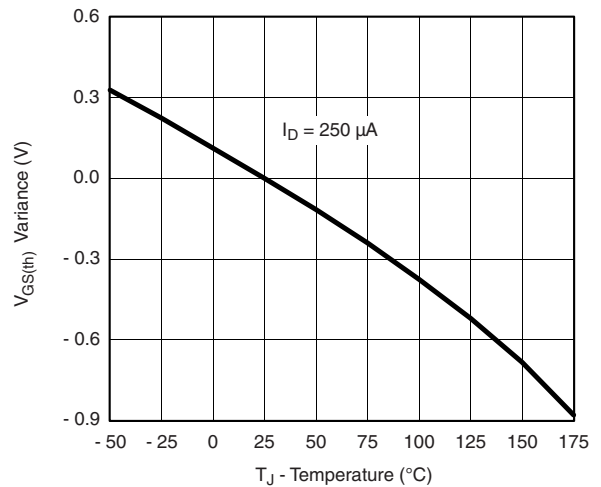
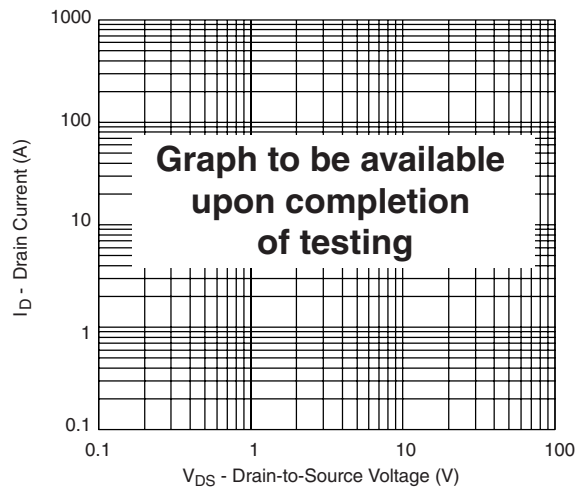
Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted

Output Characteristics

Transfer Characteristics

Transconductance

On-Resistance vs. Drain Current

Capacitance

Gate Charge

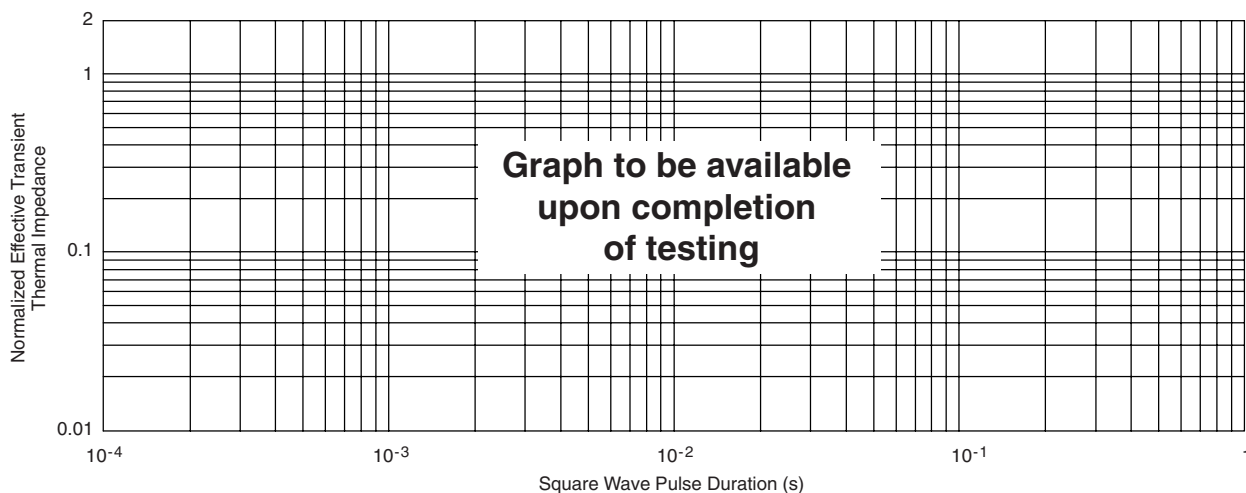
TYPICAL CHARACTERISTICS $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted**On-Resistance vs. Junction Temperature****Source Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage****Drain Source Breakdown vs. Junction Temperature**

THERMAL RATINGS $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted

Maximum Drain Current vs. Ambient Temperature

Avalanche Current vs. Time

Single Pulse Power, Junction-to-Ambient

Threshold Voltage


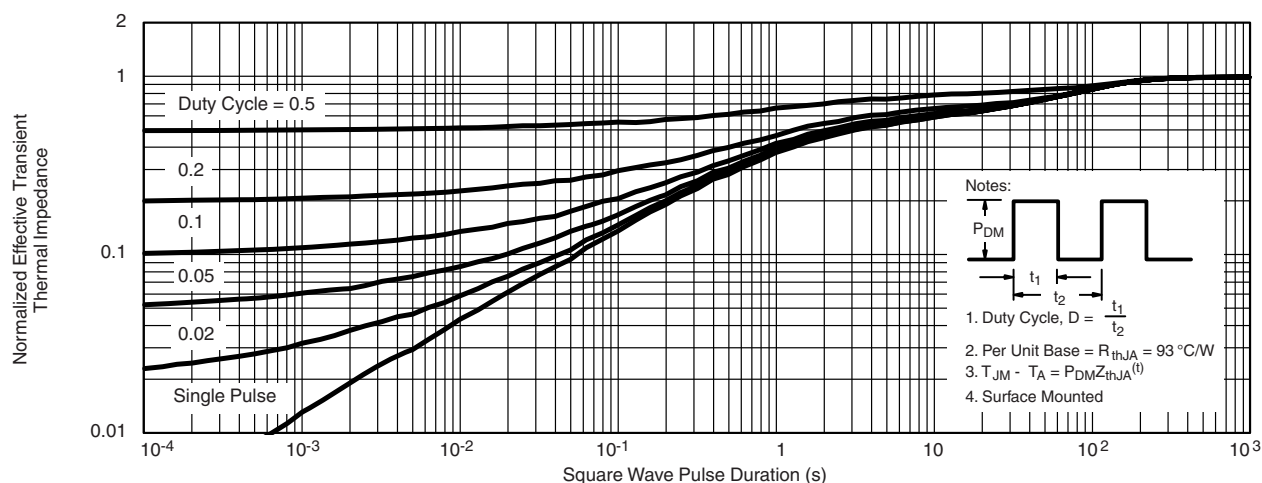
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area

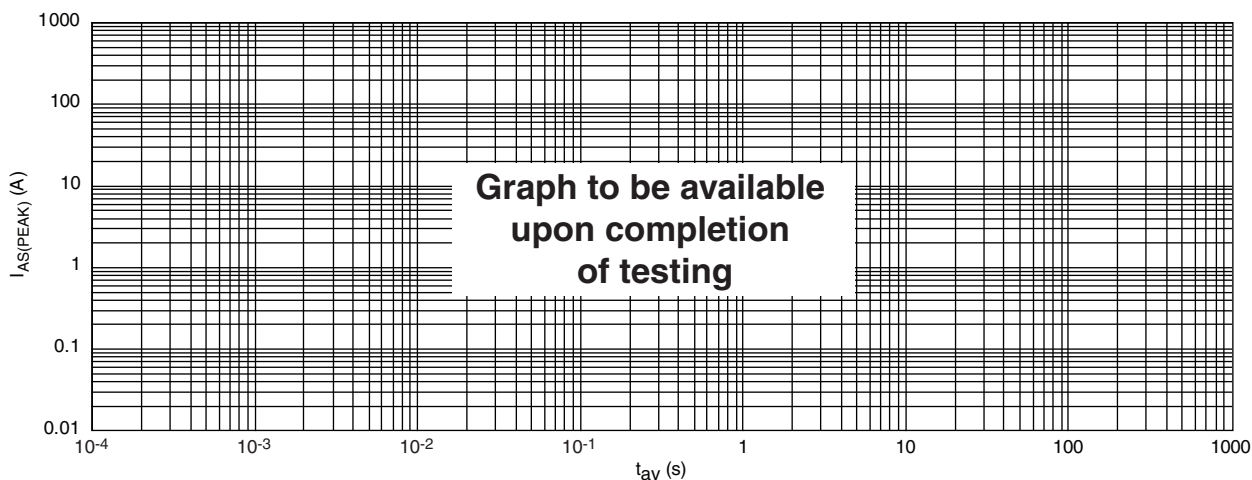
THERMAL RATINGS $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted



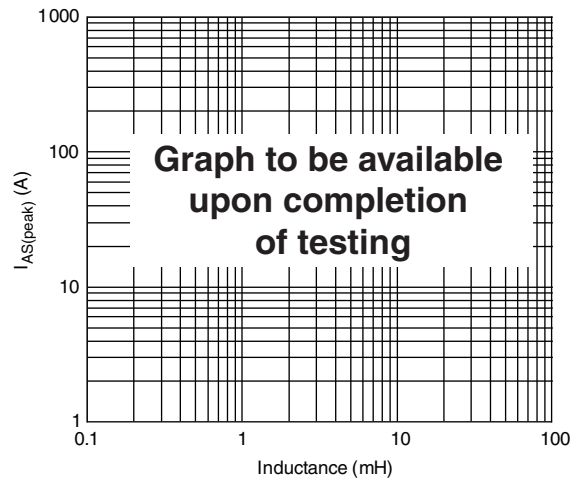
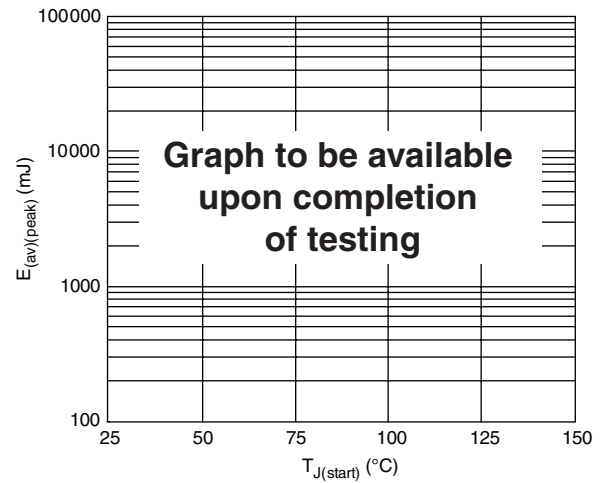
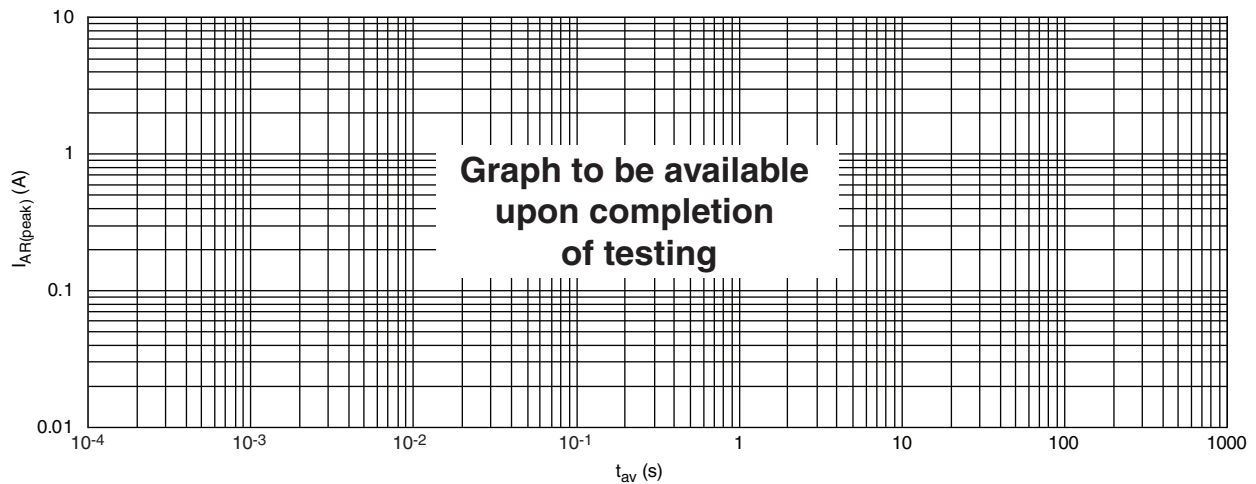
Normalized Thermal Transient Impedance, Junction-to-Case

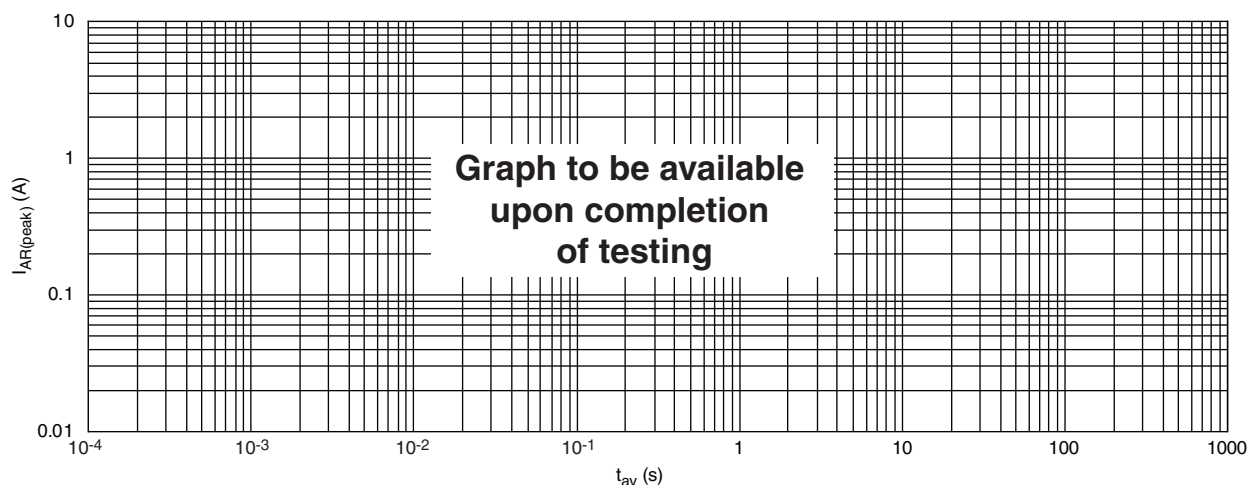


Normalized Thermal Transient Impedance, Junction-to-Ambient



Single Pulse Avalanche Current (Peak) vs. Time in Avalanche

THERMAL RATINGS $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted

Single Pulse Avalanche Current (Peak) vs. Inductance

Single Pulse Avalanche Energy (Peak) vs. $T_{J(start)}$

Repetitive Avalanche Current (Peak) vs. Time in Avalanche at $T_A = 25\text{ }^{\circ}\text{C}$

THERMAL RATINGS $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted**Repetitive Avalanche Current (Peak) vs. Time in Avalanche at $T_A = 150\text{ }^{\circ}\text{C}$** **Note**

The characteristics shown in the six graphs

- Normalized Transient Thermal Impedance Junction to Ambient ($25\text{ }^{\circ}\text{C}$)
- Single Pulse Avalanche Current (Peak) vs. Time in Avalanche
- Single Pulse Avalanche Current (Peak) vs. Inductance
- Single Pulse Avalanche Energy (Peak) vs. $T_{J(\text{start})}$
- Repetitive Avalanche Current (Peak) vs. Time in Avalanche at $T_A = 25\text{ }^{\circ}\text{C}$
- Repetitive Avalanche Current (Peak) vs. Time in Avalanche at $T_A = 150\text{ }^{\circ}\text{C}$

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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